

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- · Soft recovery minimizes power-consuming oscillations

3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	150	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2		-	-	8	A
Static characteristics							
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>		-	0.92	1.05	V
Dynamic chara	acteristics			·	·		_
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5; Fig. 7$		-	20	25	ns
Electrostatic discharge							
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K — A 001aaa020
2	А	anode	$2 \circ 4$	001aaa020
mb	mb	mounting base; cathode	C () () () () () () () () () ()	

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BYW29E-150	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Limiting values

Table 4.Limiting values

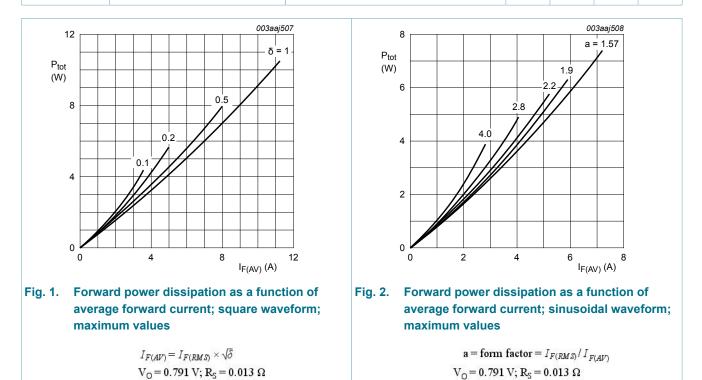
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{RRM}	repetitive peak reverse voltage		-	150	V
V _{RWM}	crest working reverse voltage		-	150	V
V _R	reverse voltage		-	150	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 128 °C; square-wave pulse	-	16	A
I _{FSM}	non-repetitive peak forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	88	A
		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	80	A
I _{RRM}	repetitive peak reverse current	δ = 0.001 ; t _p = 2 μs	-	0.2	А

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Symbol	Parameter	Conditions		Min	Max	Unit	
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs		-	0.2	A	
T _{stg}	storage temperature			-40	150	°C	
Tj	junction temperature			-	150	°C	
Electrostatic discharge							
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	8	kV	

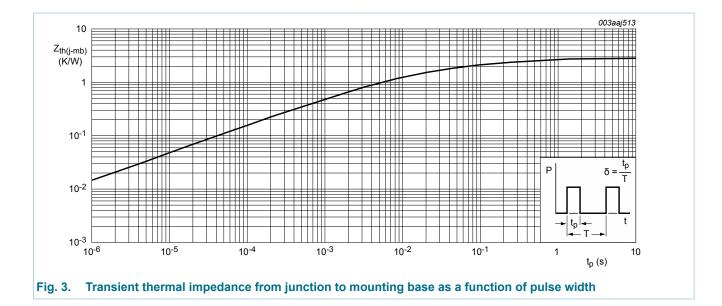


8. Thermal characteristics

Table 5. Th	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

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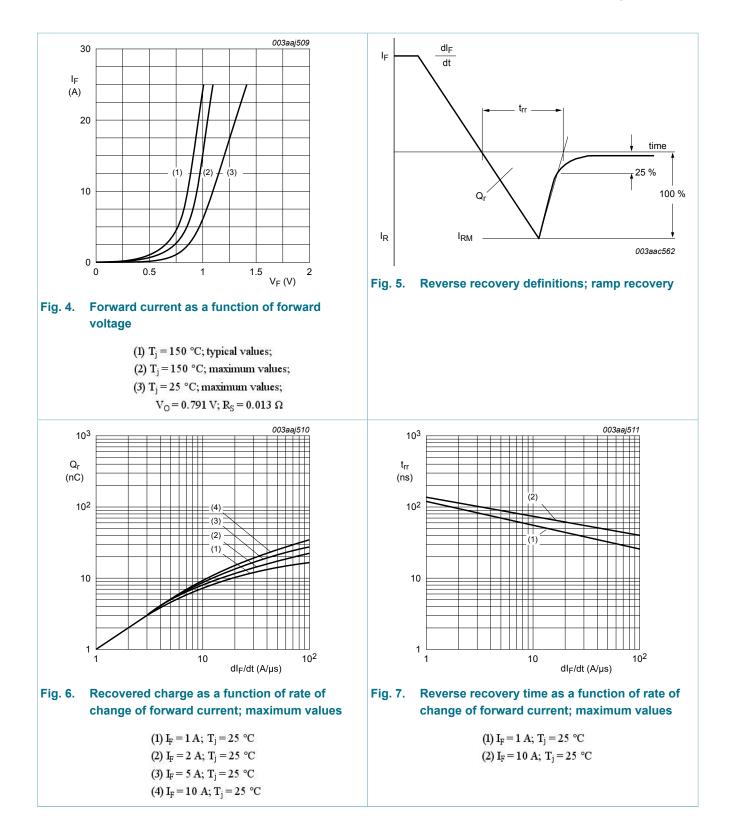


9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · · · ·				,
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>	-	0.92	1.05	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.3	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
I _R	reverse current	V _R = 150 V; T _j = 25 °C	-	2	10	μA
		V _R = 150 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic cł	naracteristics	· · · · ·				
Qr	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A}/\mu\text{s};$ T _j = 25 °C; Fig. 5; Fig. 6	-	4	11	nC
t _{rr} reverse recovery		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5; Fig. 7$	-	20	25	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ step recovery}; Fig. 8$	-	15	20	ns
V _{FRM}	forward recovery voltage	I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; Fig. 9	-	1	-	V

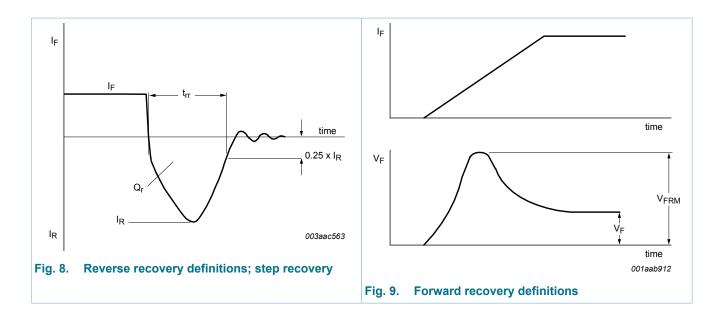
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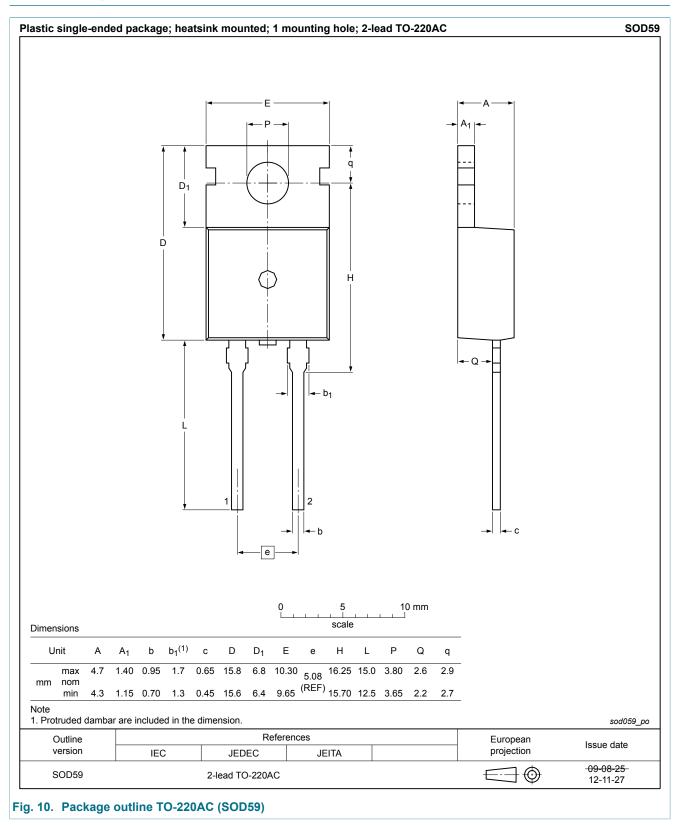
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10. Package outline



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Product data sheet

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11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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The term 'short data sheet' is explained in section "Definitions". [2]

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